

# Simulation and hit reconstruction of irradiated pixel sensors for the CMS experiment

E. Alagöz<sup>a</sup>, V. Chiochia<sup>a,\*</sup>, M. Swartz<sup>b</sup>

<sup>a</sup>Physik Institut der Universität Zürich-Irchel, 8057 Zürich, Switzerland

<sup>b</sup>Johns Hopkins University, Baltimore, MD 21218, USA

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## Abstract

In this paper a detailed simulation of irradiated pixel sensors was used to investigate the effects of radiation damage on the position determination and optimize the hit reconstruction algorithms. The simulation implements a model of radiation damage by including two defect levels with opposite charge states and trapping of charge carriers. The simulation shows that a position resolution below  $15 \mu\text{m}$  along the CMS  $r - \phi$  plane can be achieved after an irradiation fluence of  $5.9 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$ . In addition, we show that systematic errors in the position determination can be largely reduced by applying  $\eta$  corrections.

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## 1. Introduction

The CMS experiment, currently under construction at the Large Hadron Collider (LHC) will include a silicon pixel detector [1] to allow tracking in the region closest to the interaction point. The detector will be a key component for reconstructing interaction vertices and heavy quark decays in a particularly harsh environment, characterized by a high track multiplicity and heavy irradiation. At the full LHC luminosity the innermost layer, with a radius of 4.3 cm, will be exposed to a particle fluence of  $3 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2/\text{yr}$ .

In order to evaluate the effects of irradiation and optimize the algorithms for the position determination a detailed simulation of the pixel sensors was implemented. In [2] we have proved that it is possible to adequately describe the charge collec-

tion characteristics of a heavily irradiated silicon detector in terms of a tuned double junction model which produces a doubly peaked electric field profile across the sensor. The modeling is supported by the evidence of doubly peaked electric fields obtained from beam test measurements and presented in [3]. The dependence of the modeled trap concentrations upon fluence was presented in [4] and the temperature dependence of the model was discussed in [5]. In this paper the simulation was used to study the position determination in irradiated pixel sensors.

This paper is organized as follows: the sensor simulation is described in Section 2, in Section 3 the determination of the hit position in irradiated pixel sensors is discussed. The results are presented in Section 4 and the conclusions are given in Section 5.

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\* Corresponding author

Email address: vincenzo.chiochia@cern.ch  
(V. Chiochia).

## 2. Sensor simulation

The results presented in this paper rely upon a detailed sensor simulation that includes the modeling of irradiation effects in silicon. The simulation, PIXELAV [2, 6, 7], incorporates the following elements: an accurate model of charge deposition by primary hadronic tracks (in particular to model delta rays); a realistic 3-D intra-pixel electric field map; an established model of charge drift physics including mobilities, Hall Effect, and 3-D diffusion; a simulation of charge trapping and the signal induced from trapped charge; and a simulation of electronic noise, response, and threshold effects. The intra-pixel electric field map was generated using TCAD 9.0 [8] to simultaneously solve Poisson’s Equation, the carrier continuity equations, and various charge transport models.

The simulated devices correspond to the baseline sensor design for the CMS barrel pixel detector. The sensors are “n-in-n” devices, designed to collect charge from n<sup>+</sup> structures implanted into n- bulk silicon. The simulated samples were 22x32 arrays of 100x150 μm<sup>2</sup> pixels. The substrate was 285 μm thick, n-doped silicon. The donor concentration was set to 1.2 × 10<sup>12</sup> cm<sup>-3</sup> corresponding to a depletion voltage of about 75 V for an unirradiated device. The 4 T magnetic field was set as in the CMS configuration and the sensor temperature to -10° C. The simulation did not include the “punch-through” structure on the n<sup>+</sup> implants which is used to provide a high resistance connection to ground and to provide the possibility of on-wafer IV measurements.

The effect of irradiation was implemented in the TCAD simulation by including two defect levels in the forbidden silicon bandgap with opposite charge states and trapping of charge carriers. The activation energies of the donor and acceptor traps were set to ( $E_V + 0.48$ ) eV and ( $E_C - 0.525$ ) eV, respectively, where  $E_V$  and  $E_C$  are the valence and conduction band energy level, respectively. The trap densities and the capture cross sections for electrons and holes were obtained by fitting the model to beam test data as described in [2, 4]. The simulated irradiation fluences were  $\Phi = 2 \times 10^{14}$  n<sub>eq</sub>/cm<sup>2</sup> and  $\Phi = 5.9 \times 10^{14}$  n<sub>eq</sub>/cm<sup>2</sup> and the re-

verse bias was set to 200 V and 300 V, respectively.

The electric field profile as function of the sensor depth is shown in Fig. 1(a). The field has maxima at the detector implants and a minimum near the midplane which shifts towards the p<sup>+</sup> implant at lower fluences. The dependence of the space charge density upon the detector depth is shown in Fig. 1(b). Before irradiation the sensor is characterized by a constant and positive space charge density across the sensor bulk. At a fluence  $\Phi = 2 \times 10^{14}$  n<sub>eq</sub>/cm<sup>2</sup> the device shows a negative space charge of about  $-6 \times 10^{13}$  cm<sup>-3</sup> for most of its thickness, a compensated region corresponding to the electric field minimum and a positive space charge density close to the backplane. The space charge density and electric field near the p<sup>+</sup> implant increase with the irradiation fluence.

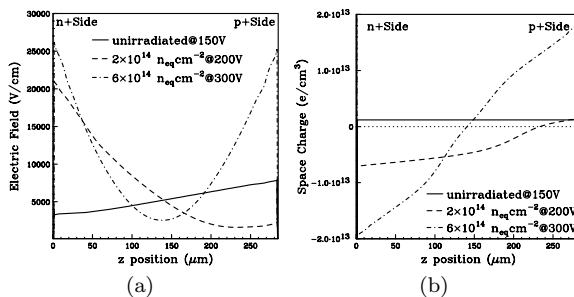


Fig. 1. The z-component of the simulated electric field (a) and space charge density (b), resulting from the two-trap model, are shown as a function of z for unirradiated and irradiated devices.

## 3. Hit reconstruction

The spatial resolution of the pixel sensors is mainly determined by the readout pitch and charge sharing between neighboring cells. Pixels have a weak capacitive coupling and charge sharing is mainly due to diffusion and drift of charge carriers under the combined effect of the magnetic and electric fields. After irradiation, free carriers trapping produces an inhomogeneous charge collection across the bulk and charge sharing between neighboring pixels becomes strongly non linear on the impact position. In addition, the beneficial effect



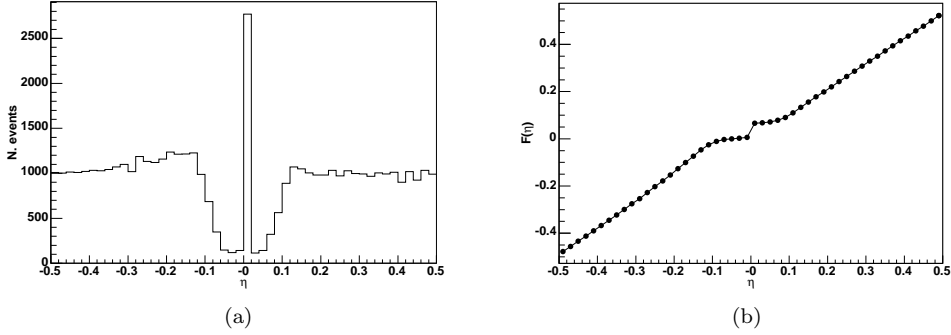


Fig. 3. (a) Distribution of the reconstructed impact position within a single pixel for perpendicular tracks. (b) Correction function  $F(\eta)$  (see Eq. 2).

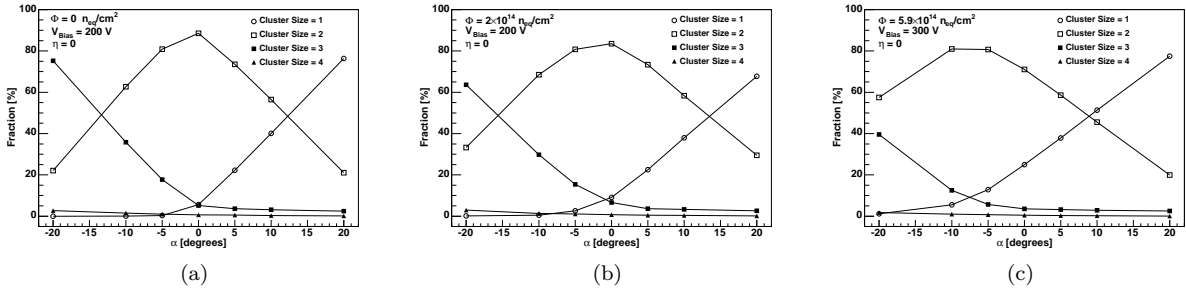


Fig. 4. Event fractions for different cluster sizes as function of the impact angle  $\alpha$  for an unirradiated sensor (a) and for sensors irradiated to  $\Phi = 2 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$  (b) and  $\Phi = 5.9 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$  (c).

$\Phi$ ( $\text{n}_{\text{eq}}/\text{cm}^2$ )	$V_{\text{bias}}$ (V)	Resolution w/o corr. ( $\mu\text{m}$ )	Resolution ( $\mu\text{m}$ )	Total Resolution ( $\mu\text{m}$ )
0	200	$9.3 \pm 0.1$	$9.1 \pm 0.1$	$9.0 \pm 0.1$
$2 \times 10^{14}$	200	$13.4 \pm 0.2$	$11.9 \pm 0.2$	$12.1 \pm 0.2$
$6 \times 10^{14}$	300	$13.3 \pm 0.1$	$12.3 \pm 0.1$	$12.9 \pm 0.1$

Table 1

Position resolution for  $\alpha = 0^\circ$  at different irradiation fluences and bias voltages. The third and fourth column show the position resolution of the two-pixel clusters without and with  $\eta$  correction, respectively. The last column shows the resolution for all events, where the position of the two-pixel clusters was  $\eta$  corrected.

um, where the position of the two-pixels clusters was  $\eta$  corrected. The simulation shows that position resolution below  $15 \mu\text{m}$  can be achieved even after heavy irradiation. In addition, the precision can be improved by correcting the reconstructed position as described in Section 3.

The size of the  $\eta$  corrections become particularly significant after irradiation and for narrow

charge widths. Figure 5 shows the residuals distribution for clusters of two pixels, simulated for a sensor irradiated to  $\Phi = 5.9 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$  and for tracks with  $\alpha = 20^\circ$ . The distribution before correction (Fig. 5(a)) is not described by a single Gaussian and is affected by large systematic errors which depend on the interpixel hit position. The distribution in Fig. 5(b) shows that the systematic

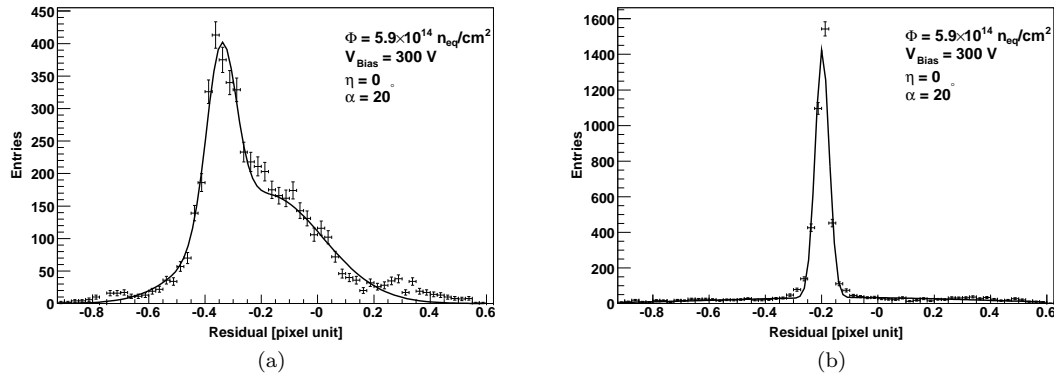


Fig. 5. Residuals distribution for tracks with  $\alpha = 20^\circ$  and a sensor irradiated to  $\Phi = 5.9 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$ . The distributions are calculated without (a) and with  $\eta$ -corrections (b) and are not corrected for the Lorentz shift due to the magnetic field. The simulated data points are represented by the markers and the continuous line is a double-Gaussian fit to the distribution.

errors can be largely reduced by applying the  $\eta$ -correction.

## 5. Conclusions

In this paper a detailed simulation of the silicon pixel sensors for the CMS tracker was used to estimate the effects of radiation damage on the position resolution. The simulation, incorporating a double junction model of radiation damage and trapping of charge carriers, provides a good description of the charge collection measurements in the fluence range from  $0.5 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$  to  $5.9 \times 10^{14} \text{ n}_{\text{eq}}/\text{cm}^2$ .

The simulation shows that a position resolution below  $15 \mu\text{m}$  can be achieved for perpendicular tracks in the CMS transverse plane even after heavy irradiation. In addition, we show that the position resolution can be improved by applying  $\eta$  corrections.

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